

NPN T-1 Standard Phototransistor

LTR-4206/LTR-4206E

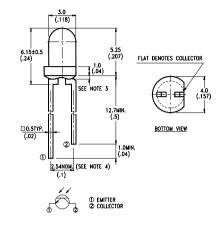
Features

- · Wide range of collector currents.
- · Lens for high sensitivity.
- · Low cost plastic package.

Description

The LTR-4206 series consist of a NPN silicon phototransistor mounted in a lensed, clear plastic, end looking package. The lensing effect of the package allows an acceptance half angle of 10° measured from the optical axis to the half power point. This series is mechanically and spectrally matched to the LTE-4206 series of infrared emitting diodes. The LTR-4206E is a special dark plastic package that cut the visible light and suitable for the detectors of infrared application.

Package Dimensions



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is \pm 0.25mm (.010") unless otherwise noted.
- 3. Protruded resin under flange is 1.5mm (.059") max.
- 4. Lead spacing is measured where the leads emerge from the package.
- 5. Specifications are subject to change without notice.

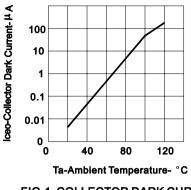
Absolute Maximum Ratings at Ta=25°C

| Parameter | Maximum Rating | Unit | | | |
|--|---------------------|------|--|--|--|
| Power Dissipation | 100 | mW | | | |
| Collector-Emitter Voltage | 30 | V | | | |
| Emitter-Collector Voltage | 5 | V | | | |
| Operating Temperature Range | -40°C to +85°C | | | | |
| Storage Temperature Range | -55°C to +100°C | | | | |
| Lead Soldering Temperature [1.6mm (.063 in.) from body] | 260°C for 5 Seconds | | | | |

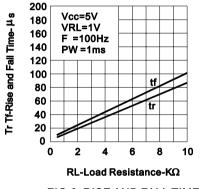
Electrical Optical Characteristics at Ta=25°C

| Parameter | Symbol | Part No. | Min. | Тур. | Max. | Unit | Test Condition |
|--------------------------------------|----------|-----------|------|------|------|------|--------------------------------------|
| Collector-Emitter Breakdown Voltage | V(BR)CEO | | 30 | | | V | Ic=1mA Ee=0mW/cm ² |
| Emitter-Collector Breakdown Voltage | V(BR)ECO | | 5 | | | V | IE=100 μ A Ee=0mW/cm ² |
| Collector Emitter Saturation Voltage | VCE(SAT) | | | | 0.4 | V | Ic=100 μ A Ee=1mW/cm ² |
| Rise Time | Tr | | | 10 | | μS | Vcc=5V Ic=1mA |
| Fall Time | Tf | | | 15 | | μS | R∟=1K Ω |
| Collector Dark Current | ICEO | | | | 100 | nA | Vce=10V Ee=0mW/cm ² |
| On State Collector Current | IC(ON) | LTR-4206 | 1 | 4 | | mA | VcE=5V Ee=1mW/cm ² |
| | | LTR-4206E | 1 | 2 | | | $\lambda = 940$ nm |

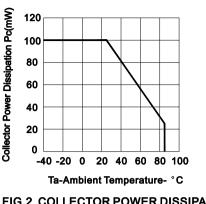
Typical Electrical/Optical Characteristic Curves (25℃ Ambient Temperature Unless Otherwise Noted)



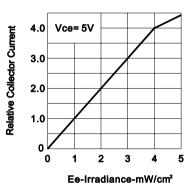














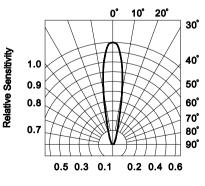


FIG.5 SENSITIVITY DIAGRAM